

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****General Description**

The AH276 is an integrated Hall sensor with output driver designed for electronic commutation of brushless DC motor applications. The device includes an on-chip Hall sensor for magnetic sensing, an amplifier that amplifies the Hall voltage, a Schmitt trigger to provide switching hysteresis for noise rejection, a temperature compensation circuit to compensate the temperature drift of Hall sensitivity and two complementary open-collector drivers for sinking large load current. It also includes an internal band-gap regulator which is used to provide bias voltage for internal circuits.

Placing the device in a variable magnetic field, if the magnetic flux density is larger than threshold B_{OP} , the pin DO will be turned low (on) and pin DOB will be turned high (off). This output state is held until the magnetic flux density reverses and falls below B_{RP} , then causes DO to be turned high (off) and DOB turned low (on).

AH276 is available in TO-94 (SIP-4L) package.

Features

- On-Chip Hall Sensor
- 3.5V to 16V Supply Voltage
- 350mA (avg) Output Sink Current
- Reversed Supply Voltage Protection
- Build in Over Temperature Protection Function
- -20°C to 85°C Operating Temperature
- Low Profile TO-94 (SIP-4L) Package
- ESD Rating: 300V (Machine Model)

Applications

- Dual-Coil Brushless DC Motor
- Dual-Coil Brushless DC Fan
- Revolution Counting
- Speed Measurement

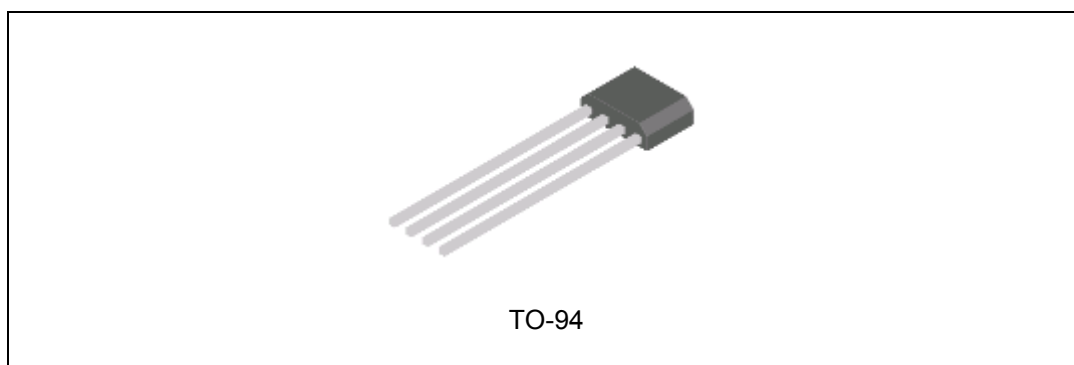


Figure 1. Package Type of AH276

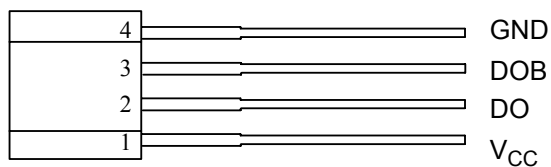
**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Pin Configuration**Z4 Package
(TO-94)

Figure 2. Pin Configuration of AH276 (Front View)

Pin Description

Pin Number	Pin Name	Function
1	V _{CC}	Supply voltage
2	DO	Output 1
3	DOB	Output 2
4	GND	Ground

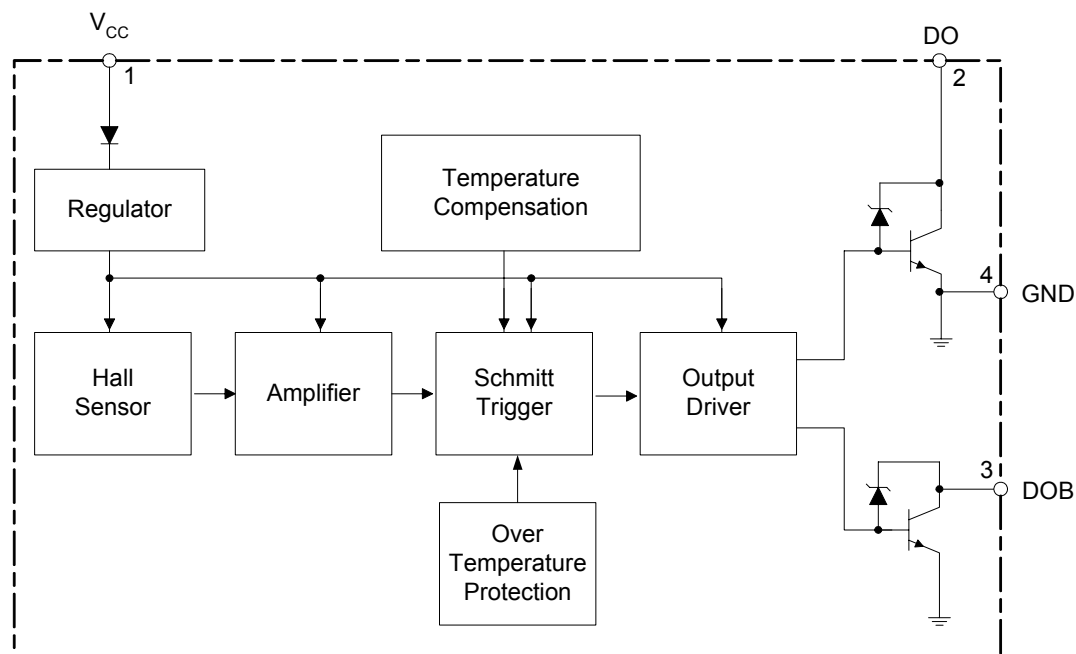
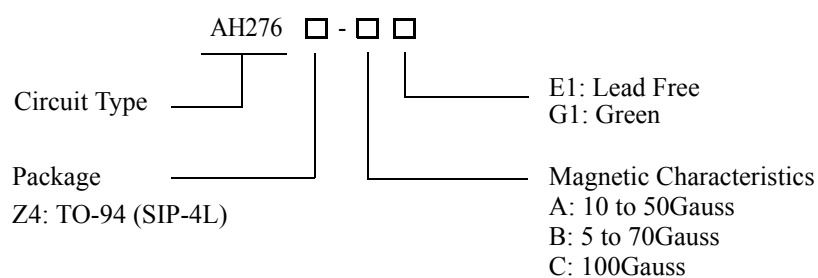
**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Functional Block Diagram**

Figure 3. Functional Block Diagram of AH276

Ordering Information

Package	Temperature Range	Part Number		Marking ID		Packing Type
		Lead Free	Green	Lead Free	Green	
TO-94	-20 to 85 °C	AH276Z4-AE1	AH276Z4-AG1	AH276Z4-E1	AH276Z4-G1	Bulk
		AH276Z4-BE1	AH276Z4-BG1	AH276Z4-E1	AH276Z4-G1	Bulk
		AH276Z4-CE1	AH276Z4-CG1	AH276Z4-E1	AH276Z4-G1	Bulk

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green package.

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Absolute Maximum Ratings (Note 1)**(T_A=25°C)

Parameter		Symbol	Value	Unit
Supply Voltage		V _{CC}	20	V
Reverse Protection Voltage		V _{RCC}	-20	V
Magnetic Flux Density		B	Unlimited	Gauss
Output Current	Continuous	I _O	350	mA
	Hold		550	mA
	Peak (start up)		750	mA
Power Dissipation		P _D	550	mW
Thermal Resistance	Die to atmosphere	θ _{JA}	227	°C/W
	Die to package case	θ _{JC}	49	°C/W
Storage Temperature		T _{STG}	-50 to 150	°C
ESD (Machine Model)			300	V
ESD (Human Body Model)			2500	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. "Absolute Maximum Ratings" for extended period may affect device reliability.

Recommended Operating Conditions(T_A=25°C)

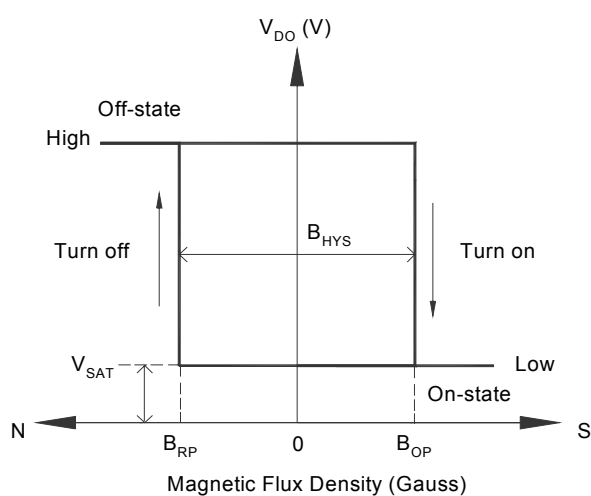
Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	3.5	16	V
Ambient Temperature	T _A	-20	85	°C

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Electrical Characteristics** $(T_A=25^{\circ}\text{C}, V_{CC}=14\text{V}, \text{ unless otherwise specified})$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Saturation Voltage	V_{SAT}	$V_{CC}=3.5\text{V}, I_O=100\text{mA}$		0.3		V
		$I_O=350\text{mA}$		0.35	0.6	V
Output Leakage Current	I_{OL}	$V_{CE}=16\text{V}$		0.1	10	μA
Supply Current	I_{CC}	$V_{CC}=16\text{V}$, Output Open		12	16	mA
Output Rise Time	t_r	$R_L=820\Omega, C_L=20\text{pF}$		3.0	10	μs
Output Fall Time	t_f	$R_L=820\Omega, C_L=20\text{pF}$		0.3	1.5	μs
Switch Time Differential	Δt	$R_L=820\Omega, C_L=20\text{pF}$		3.0	10	μs
Output Zener Breakdown Voltage	V_Z			55		V
Thermal Protection Temperature	TSD			178		$^{\circ}\text{C}$
Thermal Protection Hysteresis	ΔTSD			40		$^{\circ}\text{C}$

Magnetic Characteristics $(T_A=25^{\circ}\text{C})$

Parameter	Symbol	Grade	Min	Typ	Max	Unit
Operating Point	B_{OP}	A	10		50	Gauss
		B	5		70	Gauss
		C			100	Gauss
Releasing Point	B_{RP}	A	-50		-10	Gauss
		B	-70		-5	Gauss
		C	-100			Gauss
Hysteresis	B_{HYS}			75		Gauss



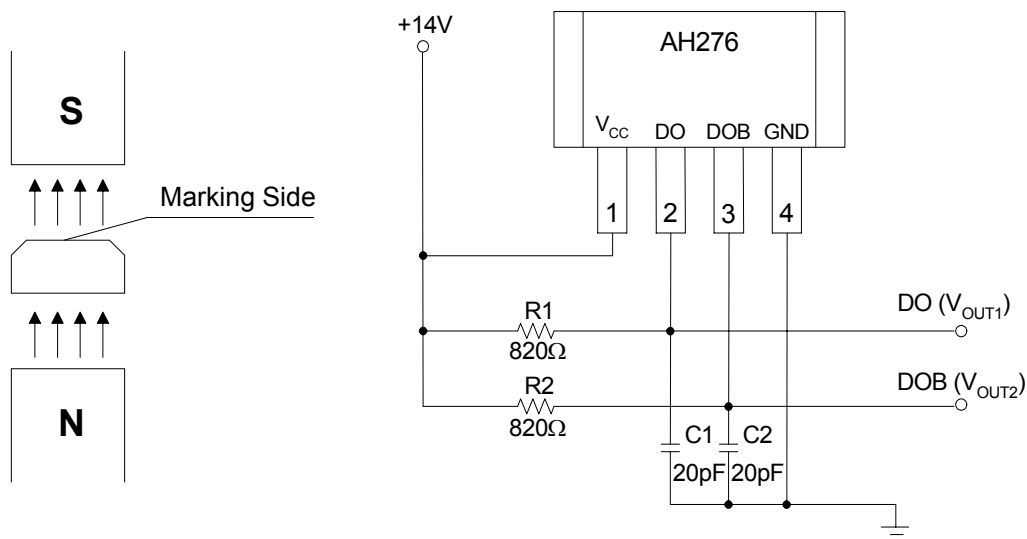
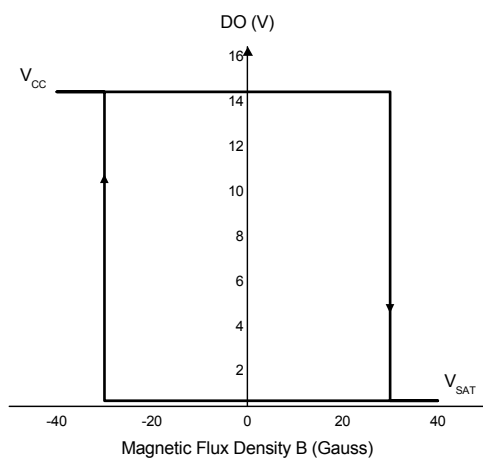
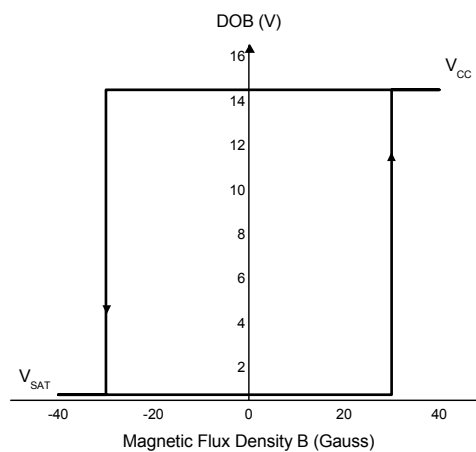
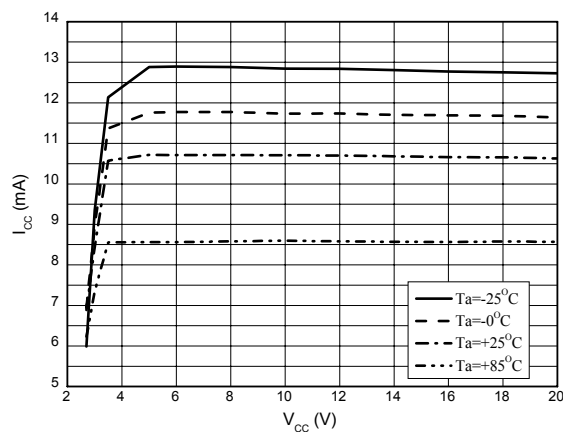
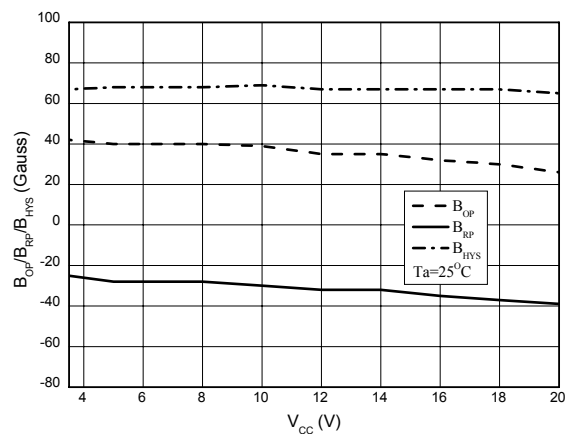
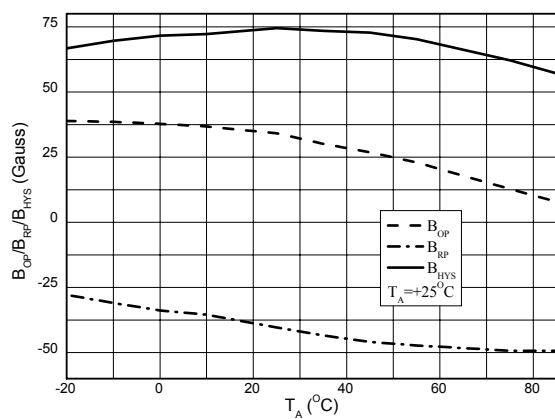
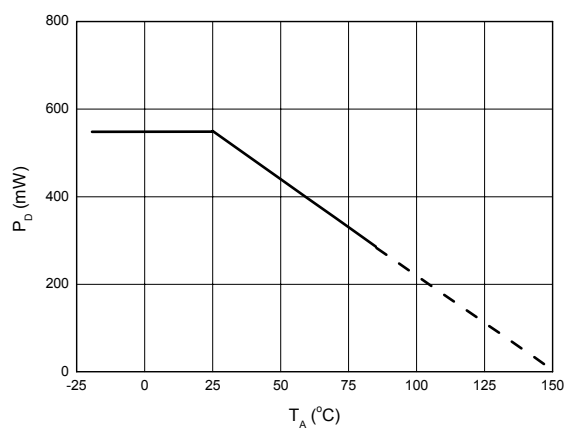
COMPLEMENTARY OUTPUT HALL EFFECT LATCH
AH276
Magnetic Characteristics (Continued)


Figure 4. Basic Test Circuit


Figure 5. V_{DO} vs. Magnetic Flux Density

Figure 6. V_{DOB} vs. Magnetic Flux Density

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Typical Performance Characteristics**Figure 7. I_{CC} vs. V_{CC} Figure 8. $B_{OP}/B_{RP}/B_{HYS}$ vs. V_{CC} Figure 9. $B_{OP}/B_{RP}/B_{HYS}$ vs. Ambient TemperatureFigure 10. P_D vs. Ambient Temperature

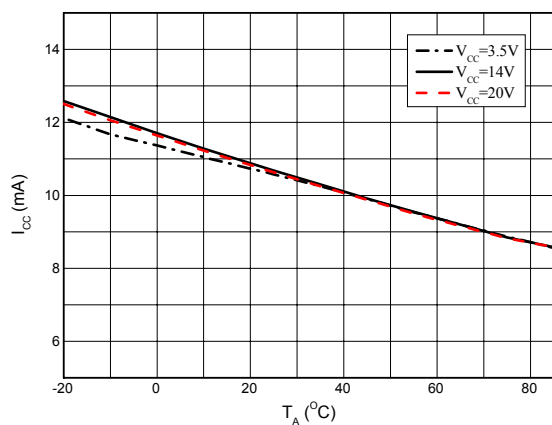
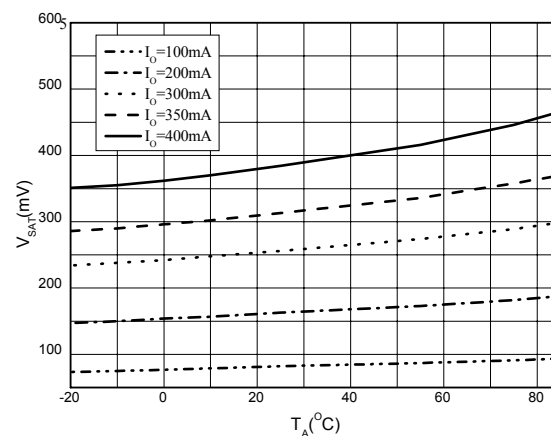
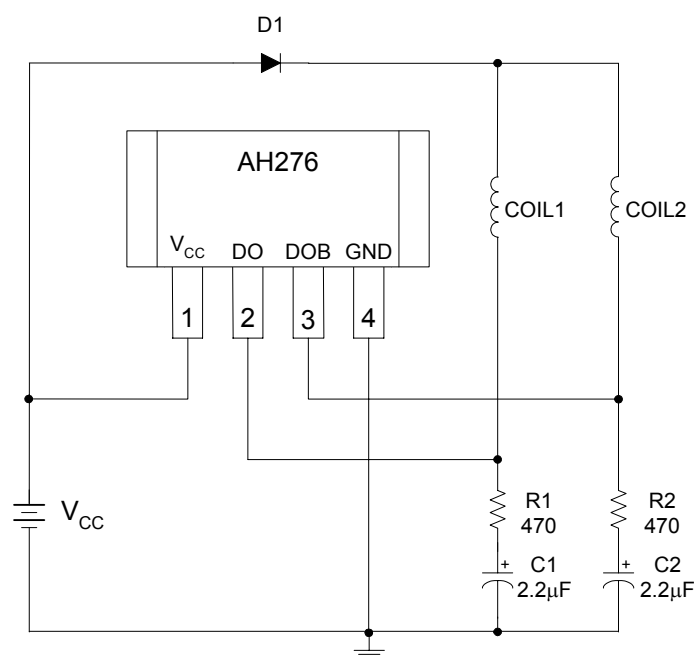
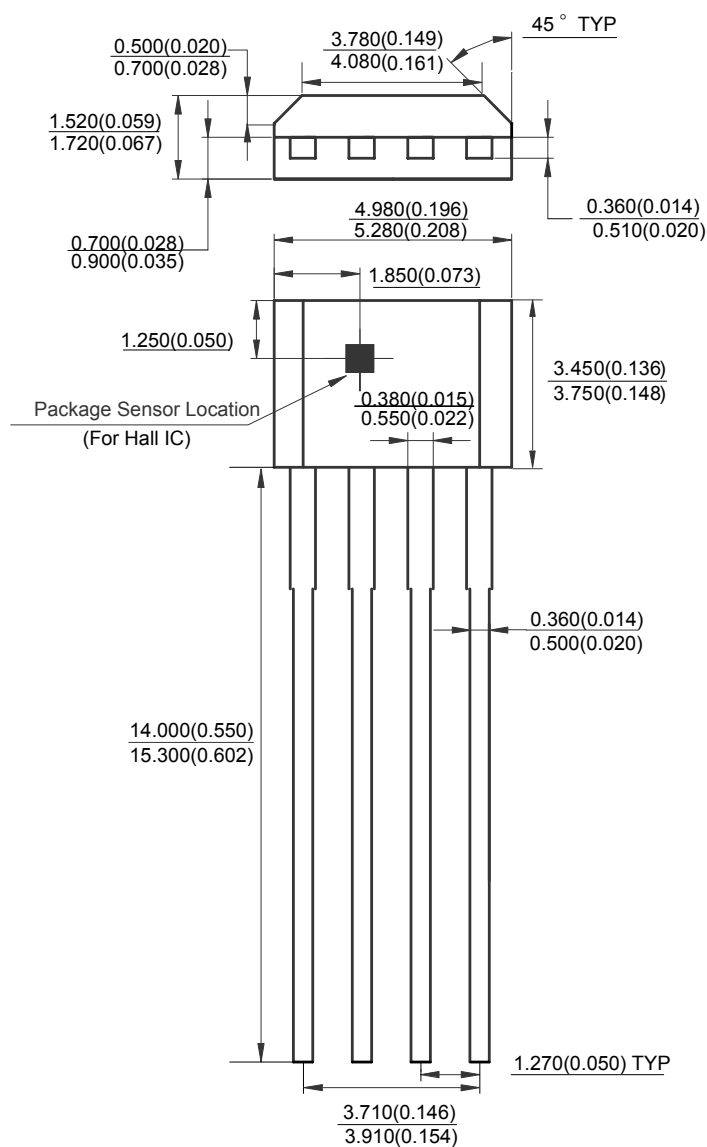
**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Typical Performance Characteristics (Continued)**Figure 11. I_{CC} vs. Ambient TemperatureFigure 12. V_{SAT} vs. Ambient Temperature**Typical Applications**

Figure 12. Typical Application Circuit

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Mechanical Dimensions****TO-94****Unit: mm(inch)**



BCD Semiconductor Manufacturing Limited

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